# NEC

# **PNP SILICON TRANSISTOR** 2SA952

### DESCRIPTION

The 2SA952 is designed for use in output stage of portable radio and cassette type tape recorder, general purpose applications.

**FEATURES** 

• High total power dissipation.

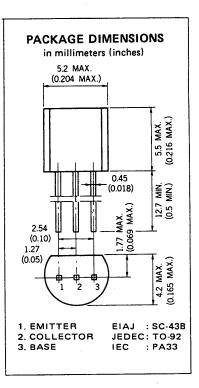
 $P_{T} = 600 \text{ mW}$ 

• High  $h_{FE}$  and low  $V_{CE(sat)}$ .  $h_{FE} (I_C = -100 \text{ mA}) : 200 \text{ TYP}.$ V<sub>CE(sat)</sub> (-700 mA) : -0.25 V TYP.

#### ABSOLUTE MAXIMUM RATINGS . .

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Maximum T	emperatures						
Storage Temperature							
Junction Temperature + 150 °C Maximum							
Maximum Power Dissipation (Ta = 25 $^{\circ}$ C)							
Total F	Power Dissipation 600	mW					
Maximum Voltages and Currents (Ta = 25 $^{\circ}$ C)							
V <sub>CBO</sub>	Collector to Base Voltage	v					
V <sub>CEO</sub>	Collector to Emitter Voltage25	v					
V <sub>EBO</sub>	Emitter to Base Voltage	V					
Ic	Collector Current	mΑ					
ł <sub>B</sub>	Base Current150	mA					



## ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1*	DC Current Gain	90	200	400	-	V <sub>CE</sub> = -1.0 V, I <sub>C</sub> = -100 mA
hFE2*	DC Current Gain	50	100		-	V <sub>CE</sub> = -1.0 V, I <sub>C</sub> = -700 mA
C <sub>ob</sub>	Collector to Base Capacitance		17	40	рF	V <sub>CB</sub> = - 6.0 V, 1 <sub>E</sub> = 0 f = 1.0 MHz
fT	Gain Bandwidth Product	50	160		MHz	$V_{CE} = -6.0 V, i_{E} = 10 mA$
V <sub>BE</sub> *	Base to Emitter Voltage	-600	-640	-700	mV	$V_{CE} = -6.0 V, I_{C} = -10 mA$
V <sub>CE(sat)</sub> *	Collector Saturation Voltage		-0.25	-0.6	V <sup>1</sup>	I <sub>C</sub> =−700 mA, I <sub>B</sub> =−70 mA
V <sub>BE(sat)</sub> *	Base Saturation Voltage		-0.95	-1.2	v	l <sub>C</sub> =-700 mA, i <sub>B</sub> =-70 mA
ICBO	Collector Cutoff Current			-100	nA	$V_{CB} = -30 V, I_{E} = 0$
IEBO	Emitter Cutoff Current			-100	nA	$V_{EB} = -5.0 V, I_{C} = 0$

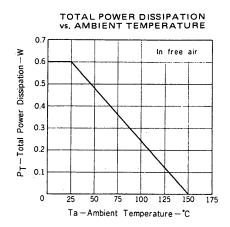
PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2.0 % \* Pulsed -

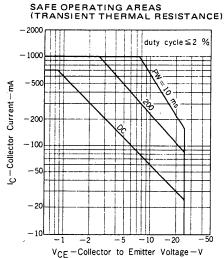
#### Classification of hFE1

Rank	м	L	к	
Range	90 - 180	135 – 270	200 – 400	

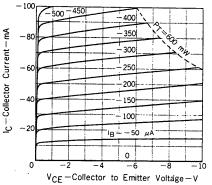
 $h_{FE}$  Test Conditions :  $V_{CE} = -1.0 V$ ,  $I_C = -100 mA$ 

#### TYPICAL CHARACTERISTICS (Ta = 25 °C unless otherwise noted)

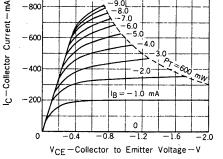




#### COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

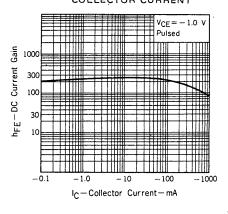


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

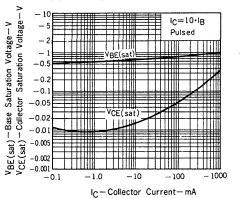


COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE - 1000 VCE = - 6.0 V - 500 Pulsed Current – mA - 200 - 100 - 50 - 20 ---Collector -10 ò -2 -0.5 -0.2

DC CURRENT GAIN vs. COLLECTOR CURRENT



BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



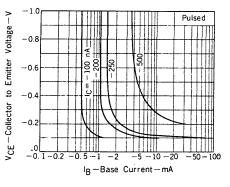
COLLECTOR TO EMITTER VOLTAGE vs. BASE CURRENT

-0.6 -0.7 -0.8 -0.9

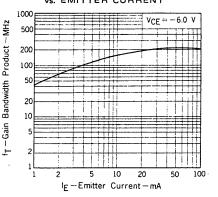
 $V_{BE}$ -Base to Emitter Voltage-V

-1.0 - 1.1

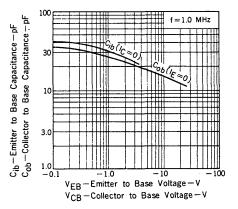
-0.1 -0.5



GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



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EMITTER TO BASE AND COLLECTOR TO BASE CAPACITANCE vs. REVERSE VOLTAGE

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